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JAPANESE PATENT OFFICE

## PATENT ABSTRACTS OF JAPAN

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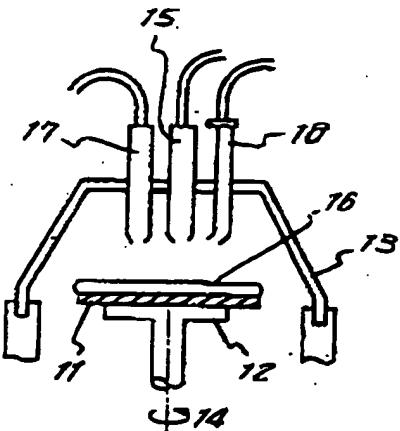
(54) DEVELOPING METHOD FOR PHOTORESIST

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(57) Abstract:

PURPOSE: To form a highly accurate photoresist pattern with high reproducibility by wetting an exposed photoresist film on a semiconductor wafer with a developing solution and then dropping the developing solution on the photoresist film to perform static development.

CONSTITUTION: While a pattern-exposed photoresist film is turned to the upper side, a semiconductor wafer 11 is fixed and rested by a vacuum chuck 12. After wetting the photoresist film by spraying a developing solution 16 from a developing nozzle 15 fitted to a developing cup 13, the prescribed volume of the developing solution 16 is dropped on the whole surface of the resist film and static development is carried out by using the developing solution kept on the resist film surface by surface tension. While the wafer 11 is being rotated together with the vacuum chuck 12 in an arrow direction, a rinsing solution is sprayed from a nozzle 17 to the wafer 11 to rinse it and then nitrogen gas or the like is sprayed to the wafer to dry it.



# EUROPEAN PATENT OFFICE

## Patent Abstracts of Japan

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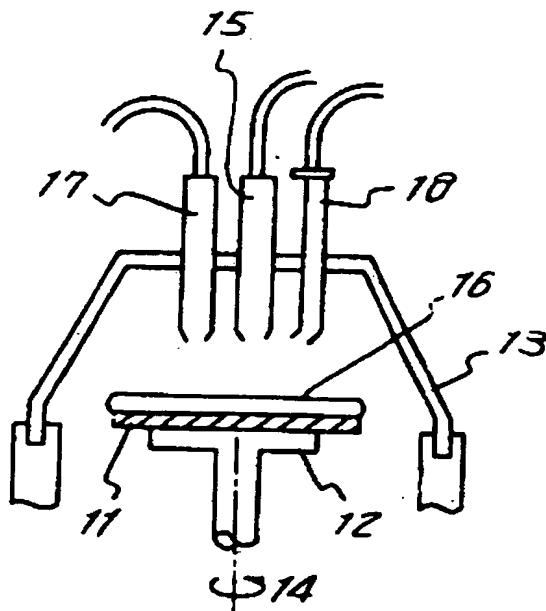
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APPLICANT : NEC CORP;

INVENTOR : YAMAZAKI KENZO;

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TITLE : DEVELOPING METHOD FOR  
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